



Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state, FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=110^\circ\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	5	mA
I_H	$I_T=0.05\text{A}$	-	-	4	mA
dV/dt	$V_D=800\text{V } T_j=110^\circ\text{C } R_{GK}=1\text{k}\Omega$	200	-	-	V/ μs
	$V_D=800\text{V } T_j=110^\circ\text{C } R_{GK}=220\Omega$	1000	-	-	



ORDERING INFORMATION

<u>J</u>	<u>X</u>	<u>014</u>	<u>CR</u>	<u>-/</u>
JieJie Microelectronics Co., Ltd.				Blank: Bulk Pack -TR: Tape & Reel
	Sensitive gate SCRs			
		Part number		
			CR:TO-92CR	

MARKING

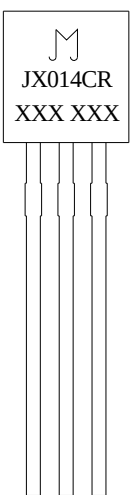
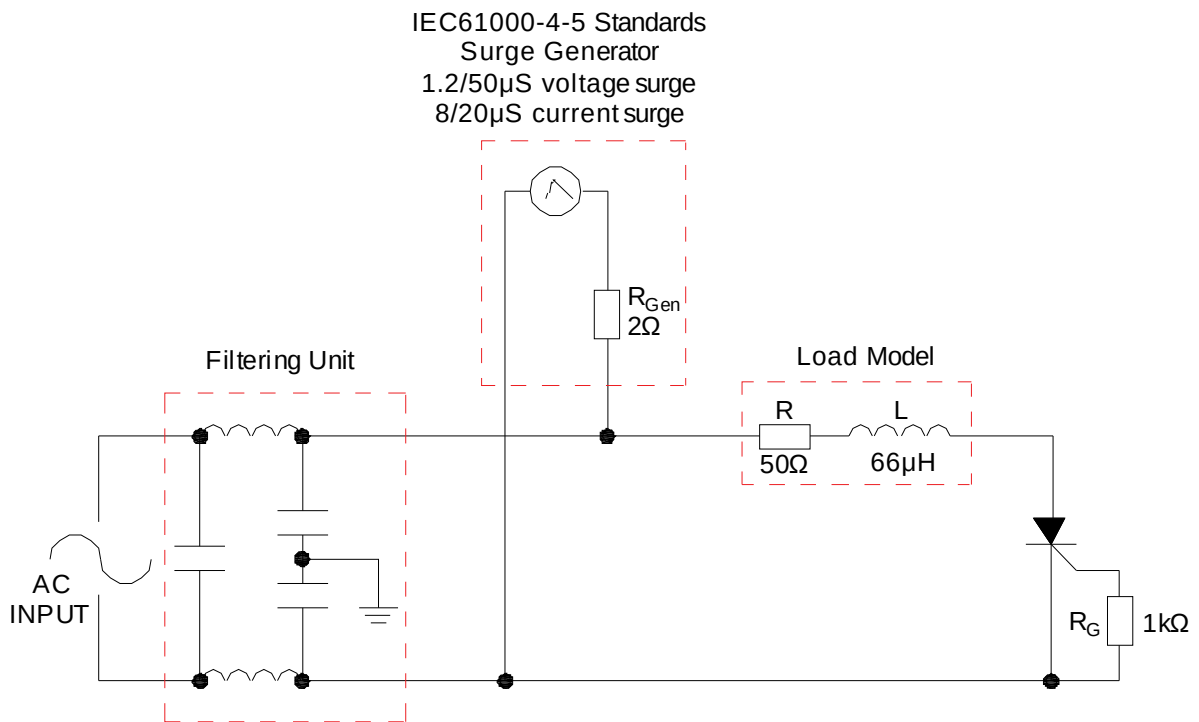
 J JX014CR XXX XXX	XXX XXX Year _____ Month _____ Production Code _____
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FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics





PACKAGE MECHANICAL DATA

